Oliver Brandt

List of Publications by Year
in descending order

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388 papers	13,079 citations	26567 56 h-index	37111 96 g-index
401 all docs	401 docs citations	401 times ranked	7461 citing authors

#	Article	IF	Citations
1	Nitride semiconductors free of electrostatic fields for efficient white light-emitting diodes. Nature, 2000, 406, 865-868.	13.7	1,662
2	Colossal Magnetic Moment of Gd in GaN. Physical Review Letters, 2005, 94, 037205.	2.9	338
3	Electronic band structure of wurtzite GaN under biaxial strain in theMplane investigated with photoreflectance spectroscopy. Physical Review B, 2002, 65, .	1.1	236
4	Direct measurement of local lattice distortions in strained layer structures by HREM. Ultramicroscopy, 1993, 49, 273-285.	0.8	202
5	Origin of high-temperature ferromagnetism in (Ga,Mn)N layers grown on 4Hâ€“SiC(0001) by reactive molecular-beam epitaxy. Applied Physics Letters, 2003, 82, 2077-2079.	1.5	197
6	Suitability of Au- and Self-Assisted GaAs Nanowires for Optoelectronic Applications. Nano Letters, 2011, 11, 1276-1279.	4.5	180
7	X-ray diffraction peak profiles from threading dislocations in GaN epitaxial films. Physical Review B, 2005, 72, .	1.1	179
8	Direct comparison of catalyst-free and catalyst-induced GaN nanowires. Nano Research, 2010, 3, 528-536.	5.8	161
9	Surface reconstructions of zinc-blende GaN/GaAs(001) in plasma-assisted molecular-beam epitaxy. Physical Review B, 1995, 52, R2253-R2256.	1.1	159
10	Impact of nucleation conditions on the structural and optical properties ofM-plane GaN(11Ì„00) grown on Î³-LiAlO2. Journal of Applied Physics, 2002, 92, 5714-5719.	1.1	143
11	Identification of optical transitions in cubic and hexagonal GaN by spatially resolved cathodoluminescence. Physical Review B, 1996, 53, 1881-1885.	1.1	142
12	High pâ€type conductivity in cubic GaN/GaAs(113)A by using Be as the acceptor and O as the codopant. Applied Physics Letters, 1996, 69, 2707-2709.	1.5	135
13	Gd-doped GaN: A very dilute ferromagnetic semiconductor with a Curie temperature above 300 K. Physical Review B, 2005, 72, .	1.1	132
14	Growth of M-plane GaN(100) on Î³-LiAlO. Journal of Crystal Growth, 2000, 218, 143-147.	0.7	131
15	Optical phonons of hexagonal and cubic GaN studied by infrared transmission and Raman spectroscopy. Applied Physics Letters, 1995, 67, 733-735.	1.5	127
16	Structural and optical properties of (100) InAs single-monolayer quantum wells in bulklike GaAs grown by molecular-beam epitaxy. Physical Review B, 1990, 41, 12599-12606.	1.1	119
17	Influence of AlN nucleation layers on growth mode and strain relief of GaN grown on 6Hâ€“SiC(0001). Applied Physics Letters, 1999, 74, 3660-3662.	1.5	113
18	Luminescence of GaAs nanowires consisting of wurtzite and zinc-blende segments. Physical Review B, 2012, 85, .	1.1	113

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19	Observation of spin-glass behavior in homogeneous (Ga,Mn)N layers grown by reactive molecular-beam epitaxy. Physical Review B, 2003, 67, .	1.1	110
20	Surface-induced effects in GaN nanowires. Journal of Materials Research, 2011, 26, 2157-2168.	1.2	107
21	Spontaneous Nucleation and Growth of GaN Nanowires: The Fundamental Role of Crystal Polarity. Nano Letters, 2012, 12, 6119-6125.	4.5	106
22	Polarity in GaN and ZnO: Theory, measurement, growth, and devices. Applied Physics Reviews, 2016, 3, .	5.5	105
23	Sub-meV linewidth of excitonic luminescence in single GaN nanowires: Direct evidence for surface excitons. Physical Review B, 2010, 81, .	1.1	104
24	Properties of GaN Nanowires Grown by Molecular Beam Epitaxy. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 878-888.	1.9	104
25	Self-Regulated Radius of Spontaneously Formed GaN Nanowires in Molecular Beam Epitaxy. Nano Letters, 2013, 13, 3274-3280.	4.5	104
26	InAs quantum dots in a single-crystal GaAs matrix. Physical Review B, 1991, 44, 8043-8053.	1.1	102
27	Direct experimental determination of the spontaneous polarization of GaN. Physical Review B, 2012, 86, .	1.1	94
28	Polarization anisotropy of the photoluminescence of M-plane (In,Ga)N/GaN multiple quantum wells. Applied Physics Letters, 2003, 82, 3850-3852.	1.5	92
29	Luminescence associated with stacking faults in GaN. Journal Physics D: Applied Physics, 2014, 47, 423001.	1.3	92
30	NonpolarInxGa1âˆ’xN/GaN(11Â¯00)multiple quantum wells grown onÎ³âˆ’LiAlO2(100)by plasma-assisted molecular-beam epitaxy. Physical Review B, 2003, 67, .	1.1	91
31	Determination of strain state and composition of highly mismatched group-III nitride heterostructures by x-ray diffraction. Journal Physics D: Applied Physics, 2002, 35, 577-585.	1.3	89
32	Critical issues for the growth of high-quality (Al,Ga)N/GaN and GaN/(In,Ga)N heterostructures on SiC(0001) by molecular-beam epitaxy. Applied Physics Letters, 1999, 75, 4019-4021.	1.5	88
33	In-plane polarization anisotropy of the spontaneous emission of M-plane GaN/(Al,Ga)N quantum wells. Applied Physics Letters, 2000, 77, 3343-3345.	1.5	85
34	Breakdown of continuum elasticity theory in the limit of monatomic films. Physical Review Letters, 1992, 68, 1339-1342.	2.9	84
35	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Co</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> light-emitting diodes: Competition between spin injecti. Physical Review B, 2008, 78, .	1.1	84
36	Temperature dependence of the radiative lifetime in GaN. Physical Review B, 1998, 58, R15977-R15980.	1.1	83

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37	Molecular beam epitaxy of single crystalline GaN nanowires on a flexible Ti foil. Applied Physics Letters, 2016, 108, .	1.5	79
38	Exciton localization in submonolayer InAs/GaAs multiple quantum wells. Physical Review B, 1990, 42, 3209-3212.	1.1	78
39	Direct observation of the initial nucleation and epitaxial growth of metastable cubic GaN on (001) GaAs. Applied Physics Letters, 1997, 70, 583-585.	1.5	78
40	Superhigh-frequency surface-acoustic-wave transducers using AlN layers grown on SiC substrates. Applied Physics Letters, 2002, 81, 2538-2540.	1.5	76
41	Determination of the azimuthal orientational spread of GaN films by x-ray diffraction. Applied Physics Letters, 2002, 81, 4928-4930.	1.5	73
42	Molecular Beam Epitaxy of GaN Nanowires on Epitaxial Graphene. Nano Letters, 2017, 17, 5213-5221.	4.5	72
43	Impact of Internal Electric Field and Localization Effect on Quantum Well Excitons in AlGaN/GaN/InGaN Light Emitting Diodes. Physica Status Solidi A, 2001, 183, 91-98.	1.7	70
44	Controlled n-type doping of AlN:Si films grown on 6H-SiC(0001) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2005, 86, 024106.	1.5	70
45	Epitaxial Growth of GaN Nanowires with High Structural Perfection on a Metallic TiN Film. Nano Letters, 2015, 15, 3743-3747.	4.5	69
46	Metal-Exchange Catalysis in the Growth of Sesquioxides: Towards Heterostructures of Transparent Oxide Semiconductors. Physical Review Letters, 2017, 119, 196001.	2.9	68
47	All-electrical spin injection and detection in the Co2FeSi/GaAs hybrid system in the local and non-local configuration. Applied Physics Letters, 2013, 103, .	1.5	67
48	Growth of M-Plane GaN(11-00): A Way to Evade Electrical Polarization in Nitrides. Physica Status Solidi A, 2000, 180, 133-138.	1.7	64
49	Doping of group III nitrides. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 1609-1614.	0.9	63
50	Macro- and micro-strain in GaN nanowires on Si(111). Nanotechnology, 2011, 22, 295714.	1.3	61
51	Formation and morphology of InAs/GaAs heterointerfaces. Physical Review B, 1992, 45, 8443-8453.	1.1	60
52	Evaluation of the surface stoichiometry during molecular beam epitaxy of cubic GaN on (001) GaAs. Applied Physics Letters, 1996, 68, 244-246.	1.5	60
53	MBE growth of cubic GaN on GaAs substrates. Physica Status Solidi (B): Basic Research, 1996, 194, 109-120.	0.7	60
54	Growth of M-plane GaN films on Î³-LiAlO[sub 2](100) with high phase purity. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1350.	1.6	60

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55	Unpinning the Fermi level of GaN nanowires by ultraviolet radiation. Physical Review B, 2010, 82, .	1.1	60
56	Surface kinetics of zinc-blende (001) GaN. Physical Review B, 1996, 54, 4432-4435.	1.1	59
57	Valence band discontinuity at a cubic GaN/GaAs heterojunction measured by synchrotron-radiation photoemission spectroscopy. Applied Physics Letters, 1997, 70, 2407-2409.	1.5	56
58	Shallow donors in GaN studied by electronic Raman scattering in resonance with yellow luminescence transitions. Applied Physics Letters, 1996, 69, 1276-1278.	1.5	55
59	X-ray standing wave and high-resolution x-ray diffraction study of the GaAs/InAs/GaAs(100) heterointerface. Physical Review B, 1993, 48, 11496-11499.	1.1	54
60	Acoustically Driven Photon Antibunching in Nanowires. Nano Letters, 2012, 12, 252-258.	4.5	54
61	Guided propagation of surface acoustic waves in AlN and GaN films grown on4Hâ€“SiC(0001)substrates. Physical Review B, 2002, 66, .	1.1	53
62	Polarization-dependent spectroscopic study of M-plane GaN on Î³-LiAlO2. Applied Physics Letters, 2002, 80, 413-415.	1.5	53
63	Monitoring the Formation of Nanowires by Line-of-Sight Quadrupole Mass Spectrometry: A Comprehensive Description of the Temporal Evolution of GaN Nanowire Ensembles. Nano Letters, 2015, 15, 1930-1937.	4.5	53
64	Evidence of localization effects in InGaN single-quantum-well ultraviolet light-emitting diodes. Applied Physics Letters, 2000, 76, 1671-1673.	1.5	52
65	Polarization-sensitive ultraviolet photodetectors based on M-plane GaN grown on LiAlO2 substrates. Applied Physics Letters, 2006, 88, 213507.	1.5	52
66	Polarization anisotropy in GaN films for different nonpolar orientations studied by polarized photoreflectance spectroscopy. Applied Physics Letters, 2006, 88, 161920.	1.5	51
67	Current path in light emitting diodes based on nanowire ensembles. Nanotechnology, 2012, 23, 465301.	1.3	50
68	Photoluminescence from strained InAs monolayers in GaAs under pressure. Physical Review B, 1994, 50, 1575-1581.	1.1	49
69	Properties of InN layers grown on 6Hâ€“SiC(0001) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2004, 84, 1671-1673.	1.5	49
70	Ga adsorption and desorption kinetics onM-plane GaN. Physical Review B, 2004, 69, .	1.1	49
71	Nucleation, Growth, and Bundling of GaN Nanowires in Molecular Beam Epitaxy: Disentangling the Origin of Nanowire Coalescence. Nano Letters, 2016, 16, 3717-3725.	4.5	49
72	Impact of recombination centers on the spontaneous emission of semiconductors under steady-state and transient conditions. Physical Review B, 1996, 54, R5215-R5218.	1.1	48

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73	Electronic structure of cubic gallium nitride films grown on GaAs. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 819-824.	0.9	47
74	Crack-free and conductive Si-doped AlNâˆ•GaN distributed Bragg reflectors grown on 6H-SiC(0001). Applied Physics Letters, 2004, 85, 1970-1972.	1.5	46
75	Collector Phase Transitions during Vaporâ^'Solidâ^'Solid Nucleation of GaN Nanowires. Nano Letters, 2010, 10, 3426-3431.	4.5	46
76	Heavy- and light-hole character of optical transitions in InAs/GaAs single-monolayer quantum wells. Physical Review B, 1992, 45, 4217-4220.	1.1	45
77	Reactive molecular-beam epitaxy of GaN layers directly on 6Hâ€“SiC(0001). Applied Physics Letters, 1999, 75, 944-946.	1.5	44
78	Microstructure of M-plane GaN epilayers grown on Î³-LiAlO2 by plasma-assisted molecular beam epitaxy. Philosophical Magazine Letters, 2004, 84, 435-441.	0.5	44
79	Height self-equilibration during the growth of dense nanowire ensembles: Order emerging from disorder. Applied Physics Letters, 2013, 103, .	1.5	44
80	Correlation between the structural and optical properties of spontaneously formed GaN nanowires: a quantitative evaluation of the impact of nanowire coalescence. Nanotechnology, 2014, 25, 455702.	1.3	44
81	Statistical Analysis of the Shape of One-Dimensional Nanostructures: Determining the Coalescence Degree of Spontaneously Formed GaN Nanowires. Crystal Growth and Design, 2014, 14, 2246-2253.	1.4	44
82	Photoluminescence of virtualâ€surfactant grown InAs/Al0.48In0.52As single quantum wells. Applied Physics Letters, 1992, 60, 2877-2879.	1.5	43
83	The benefit of disorder. Nature Materials, 2006, 5, 769-770.	13.3	43
84	State mixing in InAs/GaAs quantum dots at the pressure-induced Î“-Xcrossing. Physical Review B, 1994, 50, 18420-18425.	1.1	42
85	In situoptical reflectometry applied to growth of indium gallium nitride epilayers and multi-quantum well structures. Semiconductor Science and Technology, 2003, 18, 212-218.	1.0	42
86	Coexistence of quantum-confined Stark effect and localized states in an (In,Ga)N/GaN nanowire heterostructure. Physical Review B, 2011, 84, .	1.1	42
87	Stacking faults as quantum wells in nanowires: Density of states, oscillator strength, and radiative efficiency. Physical Review B, 2014, 90, .	1.1	42
88	Growth mode, strain relief, and segregation of (Ga,In)Sb on GaSb(001) grown by molecular beam epitaxy. Applied Physics Letters, 1996, 68, 31-33.	1.5	41
89	Optimized growth conditions for the epitaxial nucleation of Î²-GaN on GaAs(001) by molecular beam epitaxy. Applied Physics Letters, 1997, 71, 473-475.	1.5	40
90	Recombination dynamics in GaN. Journal of Crystal Growth, 1998, 189-190, 790-793.	0.7	40

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91	Strained M-plane GaN for the realization of polarization-sensitive photodetectors. Applied Physics Letters, 2002, 81, 3380-3382.	1.5	40
92	Magnetic phases and anisotropy in Gd-dopedGaN. Physical Review B, 2006, 74, .	1.1	40
93	Observation of Dielectrically Confined Excitons in Ultrathin GaN Nanowires up to Room Temperature. Nano Letters, 2016, 16, 973-980.	4.5	40
94	Disorder-induced reversal of spin polarization in the Heusler alloy Co<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>FeSi. Physical Review B, 2011, 83, .	1.1	38
95	Optical gain in optically pumped cubic GaN at room temperature. Applied Physics Letters, 1997, 70, 1076-1077.	1.5	35
96	M-plane GaN grown on Î³-LiAlO2(100): nitride semiconductors free of internal electrostatic fields. Journal of Crystal Growth, 2001, 227-228, 437-441.	0.7	35
97	Ferrimagnetic Mn4N(111) layers grown on 6H-SiC(0001) and GaN(0001) by reactive molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 112504.	1.5	35
98	Nanowires Bending over Backward from Strain Partitioning in Asymmetric Coreâ€“Shell Heterostructures. Nano Letters, 2018, 18, 2343-2350.	4.5	35
99	Structural properties of GaN layers on Si(001) grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 1998, 83, 3800-3806.	1.1	34
100	High-Temperature Growth of GaN Nanowires by Molecular Beam Epitaxy: Toward the Material Quality of Bulk GaN. Crystal Growth and Design, 2015, 15, 4104-4109.	1.4	34
101	Triple crystal xâ€ray diffractometry of periodic arrays of semiconductor quantum wires. Applied Physics Letters, 1993, 63, 3140-3142.	1.5	33
102	Nucleation and growth of GaN layers on GaAs, Si, and SiC substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2229.	1.6	33
103	Overdamped excitations of the free electron gas in GaN layers studied by Raman spectroscopy. Physical Review B, 1998, 58, 1118-1121.	1.1	33
104	Strain Engineering of Nanowire Multi-Quantum Well Demonstrated by Raman Spectroscopy. Nano Letters, 2013, 13, 4053-4059.	4.5	33
105	Origin of the nonradiative decay of bound excitons in GaN nanowires. Physical Review B, 2014, 90, .	1.1	32
106	Effect of In segregation on the structural and optical properties of ultrathin InAs films in GaAs. Applied Physics Letters, 1992, 61, 2814-2816.	1.5	31
107	Unpinned behavior of the surface Fermi level of GaN detected by photoreflectance spectroscopy. Journal of Applied Physics, 2000, 87, 4315-4318.	1.1	31
108	Dislocation contrast in cathodoluminescence and electron-beam induced current maps on GaN(0â€‰0â€‰0â€‰1). Journal Physics D: Applied Physics, 2017, 50, 405101.	1.3	31

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109	Self-assembled formation of long, thin, and uncoalesced GaN nanowires on crystalline TiN films. Nano Research, 2018, 11, 565-576.	5.8	31
110	Picosecond dynamics of excitons in cubic GaN. Physical Review B, 1995, 52, R11615-R11618.	1.1	30
111	Cubic (In,Ga)N layers grown on GaAs(001) by dc plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 1997, 82, 1918-1920.	1.1	30
112	Very narrow-band ultraviolet photodetection based on strained M-plane GaN films. Applied Physics Letters, 2007, 90, 091110.	1.5	30
113	Single crystalline Sc2O3/Y2O3 heterostructures as novel engineered buffer approach for GaN integration on Si (111). Journal of Applied Physics, 2010, 108, 063502.	1.1	30
114	Formation of High-Quality GaN Microcrystals by Pendeoepitaxial Overgrowth of GaN Nanowires on Si(111) by Molecular Beam Epitaxy. Crystal Growth and Design, 2011, 11, 4257-4260.	1.4	30
115	Luminous Efficiency of Axial In_xGa_{1â€“x}N/GaN Nanowire Heterostructures: Interplay of Polarization and Surface Potentials. Nano Letters, 2013, 13, 3298-3304.	4.5	30
116	Optical properties of a high-quality (311)-oriented GaAs/Al0.33Ga0.67As single quantum well. Physical Review B, 1993, 48, 17599-17602.	1.1	29
117	Hot-electron photoluminescence study of the(Ga,Mn)Asdiluted magnetic semiconductor. Physical Review B, 2006, 73, .	1.1	29
118	Complete in-plane polarization anisotropy of the A exciton in unstrained A-plane GaN films. Applied Physics Letters, 2007, 91, 141903.	1.5	29
119	Electronic properties of wurtzite GaAs: A correlated structural, optical, and theoretical analysis of the same polytypic GaAs nanowire. Nano Research, 2018, 11, 4708-4721.	5.8	29
120	Optical transitions in cubic GaN investigated by spatially resolved cathodoluminescence. Applied Physics Letters, 1996, 69, 836-838.	1.5	28
121	Chapter 7 Crystal Structure of Group III Nitrides. Semiconductors and Semimetals, 1997, 50, 167-192.	0.4	28
122	Growth and mosaic model of GaN grown directly on 6Hâ€“SiC(0001) by direct current plasma assisted molecular beam epitaxy. Journal of Crystal Growth, 1998, 192, 28-32.	0.7	28
123	Inhomogeneous strain in GaN nanowires determined from x-ray diffraction peak profiles. Physical Review B, 2012, 86, .	1.1	28
124	Evidence for superradiant decay of excitons in InAs quantum sheets. Physical Review B, 1992, 45, 3803-3806.	1.1	27
125	Violet and blue emitting (In,Ga)N/GaN multiple quantum wells grown on Î³-LiAlO2(100) by radio frequency plasma-assisted molecular beam epitaxy. Applied Physics Letters, 1999, 75, 2029-2031.	1.5	27
126	Influence of heteroepitaxy on the width and frequency of the E2 (high)-phonon line in GaN studied by Raman spectroscopy. Journal of Applied Physics, 2001, 89, 3634-3641.	1.1	27

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127	Polarization filtering by nonpolar M-plane GaN films on LiAlO2. Journal of Applied Physics, 2004, 96, 7029-7035.	1.1	27
128	X-ray diffraction of epitaxial films with arbitrarily correlated dislocations: Monte Carlo calculation and experiment. Physical Review B, 2009, 80, .	1.1	27
129	Compatibility of the selective area growth of GaN nanowires on AlN-buffered Si substrates with the operation of light emitting diodes. Nanotechnology, 2015, 26, 085605.	1.3	27
130	Time-resolved photoluminescence spectroscopy of individual GaN nanowires. Physical Review B, 2012, 86, .	1.1	26
131	Sub-meV linewidth in GaN nanowire ensembles: Absence of surface excitons due to the field ionization of donors. Physical Review B, 2014, 90, .	1.1	26
132	X-ray diffraction study of corrugated semiconductor surfaces, quantum wires and quantum â˜es. Applied Surface Science, 1992, 60-61, 517-521.	3.1	25
133	Thermal stability of epitaxial Fe films on GaN(0001). Applied Physics Letters, 2009, 95, 111906.	1.5	25
134	Carrier capture by threading dislocations in (In,Ga)N/GaN heteroepitaxial layers. Physical Review B, 2010, 81, .	1.1	25
135	Mg diffusion during metalorganic vapor phase epitaxy of InP. Applied Physics Letters, 1989, 55, 1017-1019.	1.5	24
136	Growth processes and relaxation mechanisms in the molecular beam epitaxy of InAs/GaAs heterostructures. Journal of Crystal Growth, 1991, 111, 383-387.	0.7	24
137	Growth of high-quality (Al,Ga)N and (Ga,In)N heterostructures on SiC(0001) by both plasma-assisted and reactive molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2290.	1.6	24
138	Optical properties of wurtziteAlxGa1â^'xN(x<0.1) parallel and perpendicular to thecaxis. Physical Review B, 2001, 64, .	1.1	24
139	Indentation of GaN: A Study of the Optical Activity and Strain State of Extended Defects. Physica Status Solidi A, 2002, 192, 79-84.	1.7	24
140	Surface-acoustic-wave transducers for the extremely-high-frequency range using AlN/SiC(0001). Semiconductor Science and Technology, 2004, 19, 256-259.	1.0	24
141	Statistical analysis of excitonic transitions in single, free-standing GaN nanowires: Probing impurity incorporation in the poissonian limit. Nano Research, 2010, 3, 881-888.	5.8	24
142	Stochastic model for the fluctuation-limited reactionâ€“diffusion kinetics in inhomogeneous media based on the nonlinear Smoluchowski equations. Journal of Mathematical Chemistry, 2015, 53, 651-669.	0.7	24
143	Electrostatic fields and compositional fluctuations in (In,Ga)N/GaN multiple quantum wells grown by plasma-assisted molecular-beam epitaxy. Physical Review B, 2001, 64, .	1.1	23
144	In surface segregation during growth of (In,Ga)N/GaN multiple quantum wells by plasma-assisted molecular beam epitaxy. Physical Review B, 2002, 66, .	1.1	23

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145	Correlation between In content and emission wavelength of In_xGa_{1â^'x}N/GaN nanowire heterostructures. Nanotechnology, 2012, 23, 455203.	1.3	23
146	Non-destructive assessment of the polarity of GaN nanowire ensembles using low-energy electron diffraction and x-ray photoelectron diffraction. Applied Physics Letters, 2015, 106, .	1.5	23
147	Self-assembled growth of GaN nanowires on amorphous AlxOy: from nucleation to the formation of dense nanowire ensembles. Nanotechnology, 2016, 27, 325601.	1.3	23
148	Top-down fabrication of ordered arrays of GaN nanowires by selective area sublimation. Nanoscale Advances, 2019, 1, 1893-1900.	2.2	23
149	Long-wavelength (Ga, In)Sb/GaSb strained quantum well lasers grown by molecular beam epitaxy. Semiconductor Science and Technology, 1998, 13, 936-940.	1.0	22
150	Structural characterization of thin GaN epilayers directly grown on on-axis 6Hâ€“SiC(0001) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 1998, 73, 3869-3871.	1.5	22
151	Coupling of exciton states as the origin of their biexponential decay dynamics in GaN nanowires. Physical Review B, 2013, 88, .	1.1	22
152	Excitons in InAs/GaAs submonolayer quantum wells. Physical Review B, 1991, 43, 14285-14288.	1.1	21
153	Redistribution of epitaxial Si on (001) GaAs during overgrowth by GaAs. Applied Physics Letters, 1991, 59, 2730-2732.	1.5	21
154	Recombination processes and photoluminescence intensity in quantum wells under steady-state and transient conditions. Physical Review B, 1995, 51, 7029-7037.	1.1	21
155	Characterization of zinc blende InxGa1â^'xN grown by radio frequency plasma assisted molecular beam epitaxy on GaAs (001). Applied Physics Letters, 1997, 71, 909-911.	1.5	21
156	Green photoluminescence from cubic In0.4Ga0.6N grown by radio frequency plasma-assisted molecular beam epitaxy. Applied Physics Letters, 1998, 73, 1230-1232.	1.5	21
157	In surface segregation in M-plane (In,Ga)N/GaN multiple quantum well structures. Applied Physics Letters, 2003, 83, 5178-5180.	1.5	21
158	GaN nanowire templates for the pendeoepitaxial coalescence overgrowth on Si(111) by molecular beam epitaxy. Journal of Crystal Growth, 2011, 323, 418-421.	0.7	21
159	Radial Stark Effect in (In,Ga)N Nanowires. Nano Letters, 2016, 16, 917-925.	4.5	21
160	In/GaN(0001)-(3Ã—3)R30Â° adsorbate structure as a template for embedded (In, Ga)N/GaN monolayers and short-period superlattices. Applied Physics Letters, 2017, 110, .	1.5	21
161	Luminous Efficiency of Ordered Arrays of GaN Nanowires with Subwavelength Diameters. ACS Photonics, 2017, 4, 52-62.	3.2	21
162	Structural and vibrational properties of (InAs)m(GaAs)nstrained superlattices grown by molecular beam epitaxy. Journal of Applied Physics, 1991, 69, 786-792.	1.1	20

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163	Properties of cubic (In,Ga)N grown by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 73-79.	1.7	20
164	(Al,In)N layers and (Al,In)N/GaN heterostructures grown by plasma-assisted molecular beam epitaxy on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>6</mml:mn><mml:mi>H</mml:mi><mml:mtext>-SiC</mml:mtext><mml:mrow><mml:mo>(</m Physical Review B, 2008, 78, .	1.1	20
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